



N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16340Q3

FEATURES

- · Optimized for 5V Gate Drive
- Resistance Rated at V_{GS} = 2.5V
- · Ultra Low Qg and Qgd
- Low Thermal Resistance
- · Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- · Halogen Free
- SON 3.3mm x 3.3mm Plastic Package

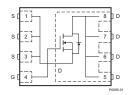
APPLICATIONS

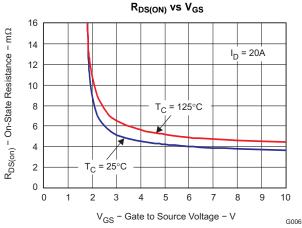
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control or Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion and optimized for 5V gate drive applications.

Figure 1. Top View





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage		V	
Q_g	Gate Charge Total (4.5V) 6.5			
Q_{gd}	Gate Charge Gate to Drain 1.2			
		$V_{GS} = 2.5V$	6.1	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$ 4.3		mΩ
		V _{GS} = 8V 3.8		mΩ
V_{th}	Threshold Voltage 0.85			

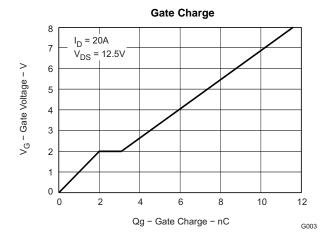
ORDERING INFORMATION

Device	Package	Package Media		
CSD16340Q3	SON 3.3 × 3.3 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -8	V
	Continuous Drain Current, T _C = 25°C	60	Α
I _D	Continuous Drain Current ⁽¹⁾	21	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	115	Α
P_D	Power Dissipation ⁽¹⁾	3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D=40A,L=0.1mH,R_G=25\Omega$	80	mJ

- (1) Typical $R_{\theta JA} = 39^{\circ} \text{C/W}$ on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics	·				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_{DS} = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V			1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.6	0.85	1.1	V
		$V_{GS} = 2.5V, I_{DS} = 20A$		6.1	7.8	$m\Omega$
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_{DS} = 20A$		4.3	5.5	$m\Omega$
		$V_{GS} = 8V, I_{DS} = 20A$		3.8	4.5	$m\Omega$
9 _{fs}	Transconductance	V _{DS} = 15V, I _{DS} = 20A		121		S
Dynamic	Characteristics					
C _{ISS}	Input Capacitance		1050 13		1350	pF
Coss	Output Capacitance	V _{GS} = 0V, V _{DS} = 12.5V, f = 1MHz		730	950	pF
C _{RSS}	Reverse Transfer Capacitance			53	69	pF
R _g	Series Gate Resistance			1.5	3	Ω
Qg	Gate Charge Total (4.5V)			6.5	9.2	nC
Q _{gd}	Gate Charge Gate to Drain	V 42.5V L 20A		1.2		nC
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_D = 20A$		2.1		nC
Qg(th)	Gate Charge at Vth			1		nC
Q _{OSS}	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$		15		nC
t _{d(on)}	Turn On Delay Time			4.8		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V I_{D} = 20A$		16.1		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$		13.8		ns
t _f	Fall Time		5.2			ns
Diode C	haracteristics					
V _{SD}	Diode Forward Voltage	I _S = 20A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	V 42V I 20A 4:/4t 20CA/:-	14.5		nC	
t _{rr}	Reverse Recovery Time	$V_{DD} = 13V$, $I_F = 20A$, $di/dt = 300A/\mu s$		20		ns

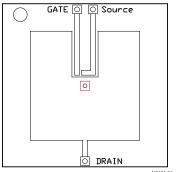
THERMAL INFORMATION

	THERMAL METRIC ⁽¹⁾⁽²⁾	CSD16340Q3	LINITO
	THERMAL METRIC (A.)	Q3 (8 PINS)	UNITS
θ_{JA}	Junction-to-ambient thermal resistance	42.0	
θ_{JCtop}	Junction-to-case (top) thermal resistance	20.6	
θ_{JB}	Junction-to-board thermal resistance	8.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	0.3	C/VV
ΨЈВ	Junction-to-board characterization parameter	8.7	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	0.1	

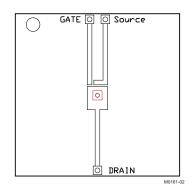
(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

(2) For thermal estimates of this device based on PCB copper area, see the TI PCB Thermal Calculator.





Max $R_{\theta JA} = 58^{\circ}C/W$ when mounted on 1 inch² of 2 oz. Cu.



Max $R_{\theta JA} = 162^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

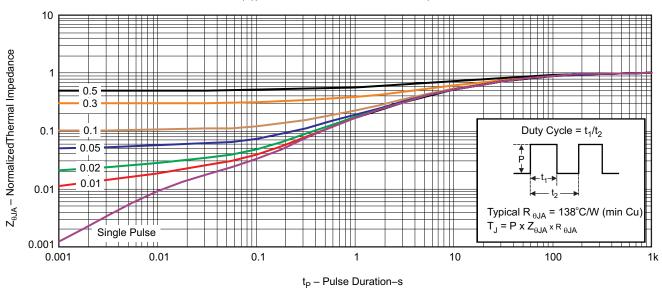


Figure 2. Transient Thermal Impedance

G012



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

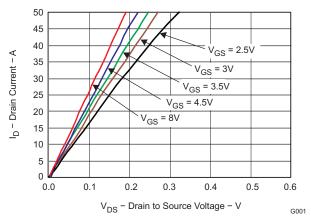


Figure 3. Saturation Characteristics

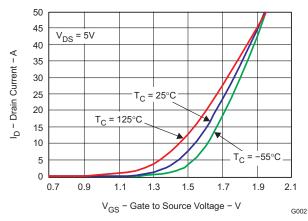


Figure 4. Transfer Characteristics

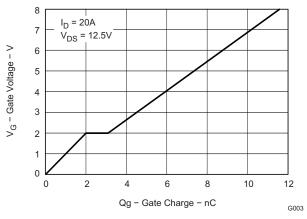


Figure 5. Gate Charge

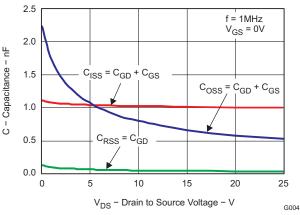


Figure 6. Capacitance

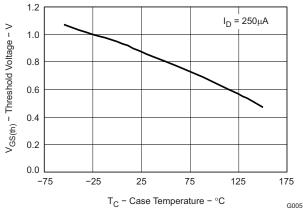


Figure 7. Threshold Voltage vs. Temperature

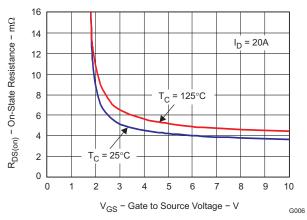


Figure 8. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

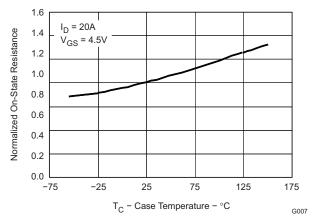


Figure 9. Normalized On Resistance vs. Temperature

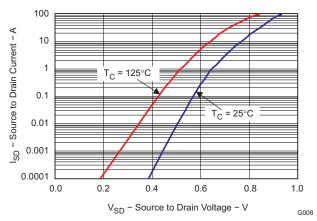


Figure 10. Typical Diode Forward Voltage

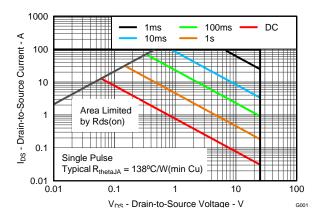


Figure 11. Maximum Safe Operating Area

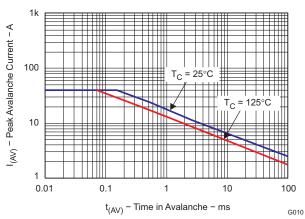


Figure 12. Single Pulse Unclamped Inductive Switching

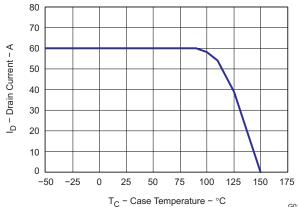
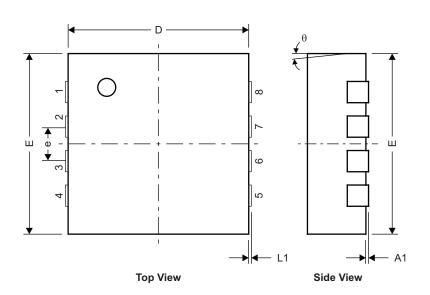


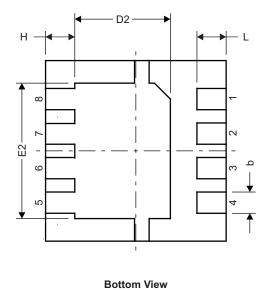
Figure 13. Maximum Drain Current vs. Temperature

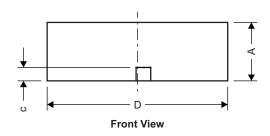


MECHANICAL DATA

Q3 Package Dimensions





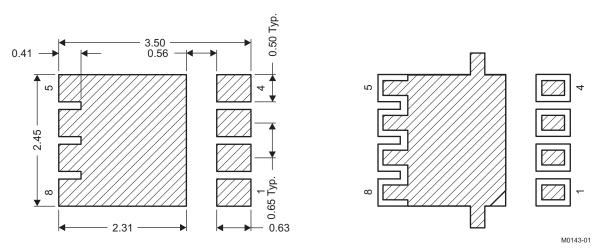


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DIM		MILLIMETERS	3	INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.950	1.000	1.100	0.037	0.039	0.043	
A1	0.000	0.000	0.050	0.000	0.000	0.002	
b	0.280	0.340	0.400	0.011	0.013	0.016	
С	0.150	0.200	0.250	0.006	0.008	0.010	
D	3.200	3.300	3.400	0.126	0.130	0.134	
D1	_	_	_	_	-	1	
D2	1.650	1.750	1.800	0.065	0.069	0.071	
Е	3.200	3.300	3.400	0.126	0.130	0.134	
E1	_	_	_	_	-	_	
E2	2.350	2.450	2.550	0.093	0.096	0.100	
е		0.650 TYP 0.026					
Н	0.35	0.450	0.550	0.014	0.018	0.022	
L	0.35	0.450	0.550	0.014	0.018	0.022	
L1	-	_	-	_	-	-	
θ	_	-	_	_	_	_	

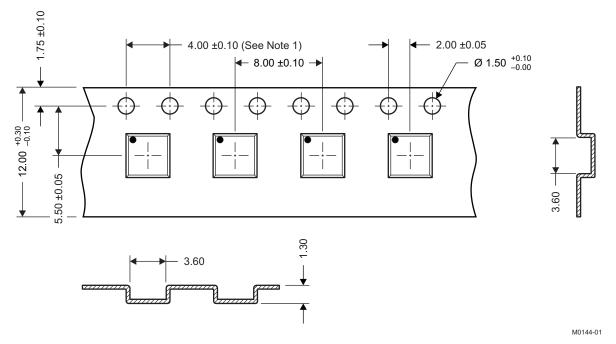


Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q3 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



REVISION HISTORY

Cł	hanges from Original (December 2009) to Revision A	Page
•	Changed Q _g in the PRODUCT SUMMARY table from: 6.8 To 6.5 nC	1
Cł	hanges from Revision A (January 2010) to Revision B	Page
•	Changed Figure 3, reversed the order of the V _{GS} labels	4
Cł	hanges from Revision B (September 2010) to Revision C	Page
•	the Package Marking Information section	7
Cł	hanges from Revision C (September 2010) to Revision D	Page
•	Replaced the THERMAL CHARACTERISTICS table with the new Thermal Information Table	2
	Replaced Figure 11 - Maximum Safe Operating Area	5

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16340Q3	SON	DQG	8	2500	330.0	12.8	3.6	3.6	1.2	8.0	12.0	Q1

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*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
I	CSD16340Q3	SON	DQG	8	2500	335.0	335.0	32.0

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